NSN 5961-01-020-3655

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View Online at https://aerobasegroup.com/nsn/5961-01-020-3655
Inclosure Material:
Metal
Overall Length:
Between 1.439 inches and 1.573 inches
Overall Diameter:
0.875 inches
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-3
Electrode Internally-electrically Connected To Case:
Collector
Internal Junction Configuration:
Pnp
Mounting Method:
Unthreaded hole
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
-80.0 collector to base voltage/static/emitter open and -80.0 collector to emitter voltage/static/base open and -5.0 emitter to base voltage
static, collector open
Current Rating Per Characteristic:
Between -7.50 amperes source cutoff current and -20.00 amperes source cutoff current
Power Rating Per Characteristic:
115.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius ambient air
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
2 pin and 1 case
Specification Data:
81349-mil-s-19500/433 government specification
Shelf Life:
N/a
Unit Of Measure:

NI

Demilitarization:

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